

Abstract

A nitride semiconductor laser device comprises a nitride semiconductor substrate (101); a nitride semiconductor lamination structure that has an n-type semiconductor layer (102), an active layer (104) and a p-type semiconductor layer (103) laminated on or above the nitride semiconductor substrate (101), and has a stripe-shaped waveguide region for laser light; and end surface protective films (110) on the both end surfaces substantially perpendicular to the waveguide region. In the nitride semiconductor laser device, the nitride semiconductor substrate (101) has a luminescent radiation region (112) that absorbs light emitted from the active layer (104) and emits luminescent radiation with a wavelength longer than the wavelength of the emitted light, and the end surface protective films (110) have a high reflectivity for the wavelength of the luminescent radiation from the luminescent radiation region (112). Accordingly, a nitride semiconductor laser device that does not improperly operate and has excellent FFP is provided.